G00002

ABSTRACT

This invention relates to a process for transfer of at least one thin film of solid material delimited in an initial substrate (20). It comprises the following steps:

- a step in which a layer of inclusions (21) is formed in the initial substrate (20) at a depth corresponding to the required thickness of the thin film, these inclusions being designed to form traps for gaseous compounds which will subsequently be implanted;
- a subsequent step for implantation of the said gaseous compounds, in a manner to convey the gaseous species into the layer of inclusions, the dose of implanted gaseous compounds being sufficient to cause the formation of micro-cavities likely to form a fracture plane along which the thin film can be separated from the remainder of the substrate.

Fig. 6B